

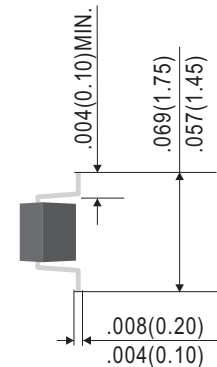
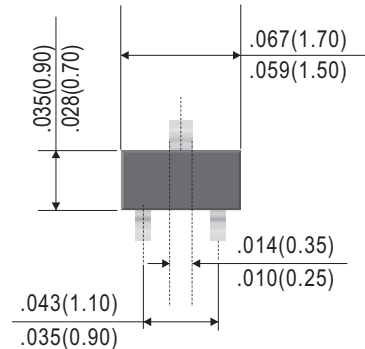
# NPN Digital Transistor

**DTC144TE**

**SOT-523**

## Features

- **Pb-Free package is available**  
RoHS product for packing code suffix "G"  
Halogen free product for packing code suffix "H"
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy



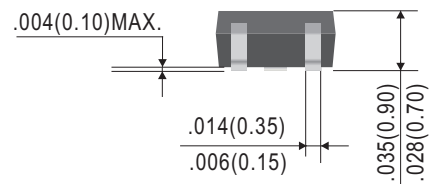
## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base voltage	$V_{EBO}$	5	V
Collector Current-Continuous	$I_C$	100	mA
Collector Dissipation	$P_C$	150	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{STG}$	-55~150	°C

## Electrical Characteristics

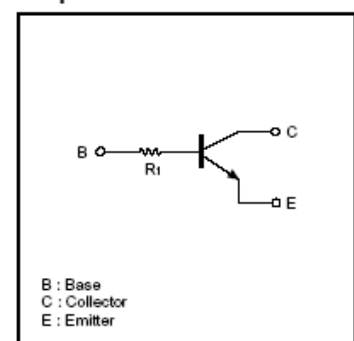
Sym	Parameter	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_C=50\mu A, I_E=0$ )	50	---	---	V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ( $I_C=1mA, I_B=0$ )	50	---	---	V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_E=50\mu A, I_C=0$ )	5	---	---	V
$I_{CBO}$	Collector Cut-off Current ( $V_{CB}=50V, I_E=0$ )	---	---	0.5	$\mu A$
$I_{EBO}$	Emitter Cut-off Current ( $V_{EB}=4V, I_C=0$ )	---	---	0.5	$\mu A$
$h_{FE}$	DC Current Gain ( $V_{CE}=5V, I_C=1mA$ )	100	300	600	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ( $I_C=5mA, I_B=0.5mA$ )	---	---	0.3	V
$R_1$	Input resistance	32.9	47	61.1	$K\Omega$
$f_T$	Transition Frequency ( $V_{CE}=10V, I_E=-5mA, f=100MHz$ )	---	250	---	MHz

\*Marking: 06



Dimensions in inches and (millimeters)

### Equivalent circuit





## Typical Characteristics

